

DLTS measurements on 4H-SiC JBS-diodes with boron implanted local p-n junctions

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A DLTS study of 4H-SiC-based p-n junctions fabricated by boron implantation

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Leakage currents in 4H-SiC JBS diodes

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Исследование р-п-переходов на основе 4H-SiC, изготовленных имплантацией бора, методом нестационарной емкостной спектроскопии

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